

GP1101 200mA CMOS LDO

GENERAL DESCRIPTION

The GP1101 is a 200mA Low Dropout and Micro-Power Voltage Regulator suitable for battery powered portable equipments.

The GP1101 built-in with internal low RDSON PMOS as the pass device, which does not cause extra ground current in different load and high dropout conditions. The extremely low of maximum 19uA operation current makes the chip suitable for battery-powered devices.

Built-in high precision voltage reference, and Current Limit circuits.

FEATURES

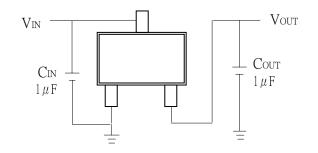
- Guaranteed 200mA Output
- Very Low Dropout Voltage of 400mV
- Iow quiescent current 19uA max.
- Output voltages range from 2.0V to 6.0V in 100mV increments
- Accuracy within ±2%
- Low Temperature Coefficient
- Built in Current and Thermal Limiting
- SOT-23 Package

APPLICATIONS

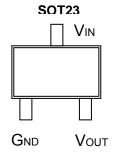
- Cellular Telephones
- Battery-powered Equipment
- Hand-held Equipment
- DSC, Laptop, Notebook, and Palmtop Computers

TYPICAL APPLICATION CIRCUIT

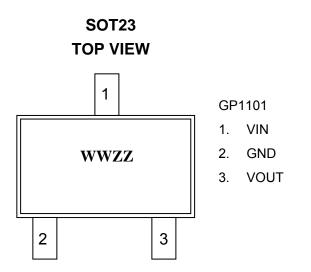
SOT23



PACKAGE PIN OUT



Package and Pin Configuration



ORDER INFORMATION

GP1101-XX 200mA Output current, SOT23 package

XX : Output voltage: 2.0V, 33: 3.3V, 50: 5.0V

Marking Information

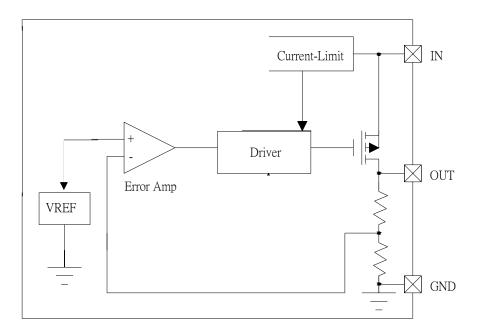
wwzz : zz : Output voltage: 2.0V, 33: 3.3V, 50: 5.0V ww : production week code

1. For other output voltages contact GPS marketing.

2. Order quantity

- SOT23 order minimum 3,000 ea per Tape/Reel
- 3. GPS Pb-free plus anneal products employ with molding compounds, die attach material and 100% matte tin plate termination finish which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations.

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS (Note a)							
Input Voltage	12V						
Continuous Total Power Dissipation, SOT-23	0.15W						
Operating Junction Temperature Range	-40℃ to 125℃						
Storage Temperature Range	-55℃ to 150℃						
Package Thermal Resistance, SOT-23, θ _{JA}	250℃/W						
Lead Temperature (Soldering, 5 sec.)	260 ℃						
Note a: Exceeding these ratings could cause damage to the device. All voltages are with	n respect to Ground.						

otor										
Parameter		Symbol V _{IN}		Recommended Operating					Units	
				Min.	Ту	/p.	Max			
				2.0			12.0		V	
Input Capacitor (V _{IN} to GND)				-					μF _	
Output Capacitor with ESR of 10Ω max.,				-			-		μF	
Ambient Temperature Range				-					°C	
Junction temperature				- 40			150		О°	
E		CHARA	СТЕ	ERISTICS						
l, V _{IN} = 5V,	C _{IN} = 1μF, C _O	_{υт} = 1μF	=, Τ,	₄ = 25°C.						
Symbol					GP1101			Units		
Symbol						Min	Тур	Max	011113	
Vo	I _O = 40mA					-2.0		2.0	%	
Ι _ο						200			mA	
ΔV_{OI}	I _O = 40mA, (Vout+1V)< V _{IN} < 10V						0.2	0.3	%V	
ΔV_{OL}	I _o =1mA to 100mA							0.04	%mA	
ΔV I _o =150mA				()			280	500	mV	
	2.	.8V	< V _o (nom))		240	450			
Ι _Q	I _O = 0mA						15	19	uA	
I _G	I _O = 100mA						15	19	μA	
I _{CL}	R_{LOAD} = 1 Ω					300			mA	
PSRR	freq = 100Hz, C _{OUT} =10μF						65		dB	
Vcoef	lout=10mA, -40 ≦Topr≦80℃						±100		ppm/°C	
	R of 10Ω m age I, $V_{IN} = 5V$, Symbol V_0 I_0 ΔV_{OL} ΔV_{OL} I_Q I	R of 10Ω max.,igeELECTRICAL (I, $V_{IN} = 5V$, $C_{IN} = 1\mu$ F, C_{OI} SymbolTe V_0 $I_0 = 40$ mA I_0 $I_0 = 40$ mA, (Vo ΔV_{OL} $I_0 = 40$ mA, (Vo ΔV_{OL} $I_0 = 1$ mA to 10 ΔV $I_0 = 1$ mA to 10 ΔV $I_0 = 150$ mA I_Q $I_0 = 0$ mA I_G $I_0 = 100$ mA I_{CL} $R_{LOAD} = 1 \Omega$ PSRRfreq = 100Hz,VcoefIout=10mA, -4	D) R of $10\Omega \text{ max.}$, nge T_A T _J ELECTRICAL CHARA I, $V_{IN} = 5V$, $C_{IN} = 1\mu$ F, $C_{OUT} = 1\mu$ F Symbol Test Cond V_O $I_O = 40$ mA I_O ΔV_{OI} $I_O = 40$ mA, (Vout+1V) ΔV_{OL} $I_O = 1$ mA to 100 mA I_O ΔV_OL $I_O = 1$ mA to 100 mA I_O $I_O = 150$ mA I_Q $I_O = 0$ mA I_Q $I_O = 0$ mA I_Q $I_O = 100$ mA I_{CL} $R_{LOAD} = 1 \Omega$ PSRR freq = 100 Hz, $C_{OUT} = 100$	D) R of 10Ω max., nge T_A T _J ELECTRICAL CHARACTI ELECTRICAL CHARACTI N V _{IN} = 5V, C _{IN} = 1µF, C _{OUT} = 1µF, T, Symbol Test Condition V ₀ I ₀ = 40mA I ₀ ΔV_{0I} I ₀ = 40mA, (Vout+1V) < V ΔV_{0L} I ₀ = 1mA to 100mA I ₀ = 150mA I ₀ = 2.8V I ₀ = 150mA I ₀ = 100mA I ₀ = 100mA I ₁ I ₀ = 100mA I ₁ R _{LOAD} = 1Ω PSRR freq = 100Hz, C _{OUT} = 10µ Vcoef Iout=10mA, -40 \leq Topr \leq	D) R of 10 Ω max., 1.0 R of 10 Ω max., 1.0 T _A - 40 T _J - 40 ELECTRICAL CHARACTERISTICS R, V _{IN} = 5V, C _{IN} = 1 μ F, C _{OUT} = 1 μ F, T _A = 25°C. Symbol Test Conditions V ₀ I ₀ = 40mA I ₀ Δ V ₀ I I ₀ = 40mA, (Vout+1V) < V _{IN} < 10V Δ V ₀ I I ₀ = 40mA, (Vout+1V) < V _{IN} < 10V Δ V ₀ I I ₀ = 100MA I ₀ = 150mA I ₀ = 2.8V 2.8V < V ₀ (nom) I ₀ = 100mA I ₁ I ₀ = 100mA I ₁ R _{LOAD} = 1 Ω PSRR freq = 100Hz, C _{OUT} = 10 μ F Vcoef Iout=10mA, -40 \leq Topr \leq 80°C	$\begin{array}{c c c c c c c c c } D) & \hline & 1.0 & \hline & 1.0 & \hline & 1.0 & \hline & & 1.0 & \hline & & & 1.0 & \hline & & & & 1.0 & \hline & & & & & & 1.0 & \hline & & & & & & & & & \\ \hline & & & & & & &$	D) 1.0 R of 10Ω max., 1.0 ige T_A - 40 T_J - 40 ELECTRICAL CHARACTERISTICS Symbol Test Conditions V_0 I_0 = 40mA -2.0 I_0 200 ΔV_{01} I_0 = 40mA, (Vout+1V) $V_{IN} < 10V$ ΔV_{0L} I_0 = 1mA to 100mA 200 ΔV_0 I_0 = 150mA $\frac{2.0V < V_0 (nom)}{< = 2.8V}$ ΔV I_0 = 100mA 2.8V $2.8V < V_0 (nom)$ $2.8V < V_0 (nom)$ I_Q I_0 = 0mA I_0 = 100mA 300 PSRR freq = 100Hz, $C_{OUT} = 10\mu F$ 300 PSRR freq = 100Hz, $C_{OUT} = 10\mu F$ V	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	

Note a: These parameters, although guaranteed, are not tested in production.

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Detailed Description

The GP1101 is 200mA CMOS LDO designed with a Low RDSON PMOS pass transistor, Bandgap voltage reference, Error amplifier, Current limit. The P-channel pass transistor receives control signal from the Error amplifier, Current limit. During normal operation, the Error amplifier compares the output voltage to an internal trimmed precision Bandgap reference to regulate and output a preset voltage.

External Capacitor Selection

The GP1101 is stable with an output capacitor to ground of 1uF or greater and > 100m ohm ESR. Ceramic or tantalum capacitors can be used. The capacitor with larger value and lower ESR provides better PSRR and line-transient response.

Ceramic capacitors have the lowest ESR, and will offer the best AC performance. Aluminum Electrolytic capacitors present the highest ESR and resulting in the poorest AC response.

In addition to the >1uF capacitor connect to Vin, recommend to add a >0.1uF capacitor between Vin to Ground to stabilize Vin.

Current Limit

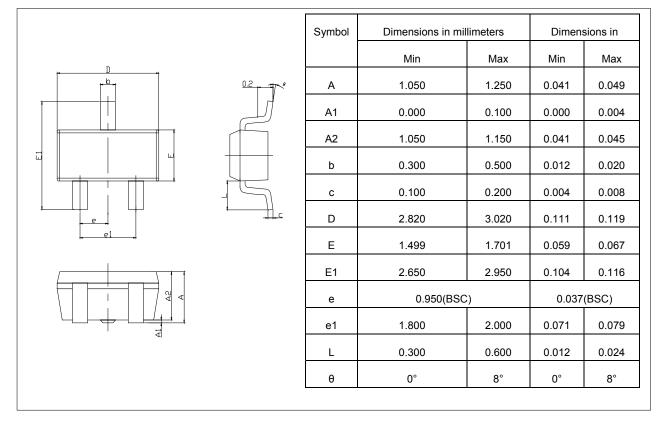
GP1101 built-in with Current Limit protection circuit, which monitors and controls the gate of the pass transistor and limiting the output current to 300mA (Min.).

Dropout Voltage

Current flow through regulator's pass PMOS transistor cause Input-Output voltage drop, it determines the lowest usable supply voltage. The GP1101 PMOS pass switch low RDSON only present 400mV dropout voltage at 100mA lout, it further extend the battery useful end-of-life voltage.

Package Information

3-Pin Surface Mount SOT23



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